



Solid State Electronics EC210
Arab Academy for Science and Technology
AAST – Cairo
Spring 2016

Lecture 9 Part b

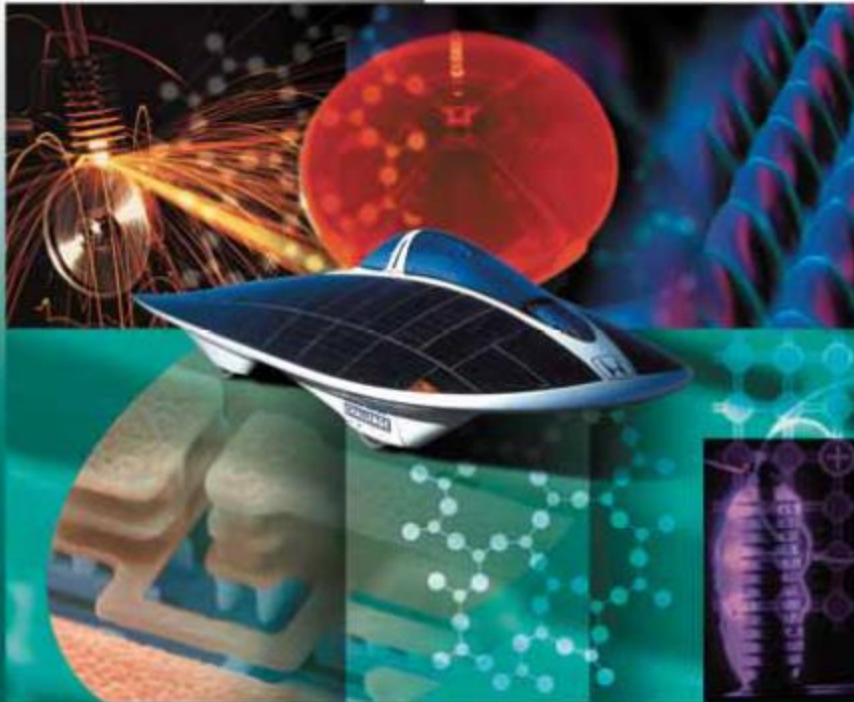
Density of States

Original Lecture Notes Prepared by:

Dr. Amr Bayoumi, Dr. Nadia Rafat

Principles of Electronic Materials and Devices

Third Edition



S. O. Kasap

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Lecture 9: part 2
Density of States

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Introduction

Given a 1D, 2D or 3D material:

How many electrons are allowed to be present within an energy band (such as valence or conduction bands)

- Must find the number of allowed “states” within an Energy range in the E-K diagram, per unit volume (or area or length) of the material
- Each state can hold up to two electrons with different spins
- The band theory does NOT allow infinite numbers of electrons within an energy range
- From the E-K diagram velocity can be found, now only the number of electrons are needed to calculate current

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Pages

- Kasap:
 - p. 305-308

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Energy Levels

- **1D ($L_x = a$) :**

$$E_n = \frac{\hbar^2 k_n^2}{2m} = \frac{h^2}{8m a^2} n^2$$

- **2D (assuming $L_x = L_y = a$):**

$$E_n = \frac{\hbar^2 k_n^2}{2m} = \frac{h^2}{8m a^2} (n_x^2 + n_y^2) = \frac{h^2}{8m a^2} n'^2$$

- **3D (assuming $L_x = L_y = L_z = a$) :**

$$E_n = \frac{\hbar^2 k_n^2}{2m} = \frac{h^2}{8m a^2} (n_x^2 + n_y^2 + n_z^2) = \frac{h^2}{8m a^2} n'^2$$

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Density of States (2D)

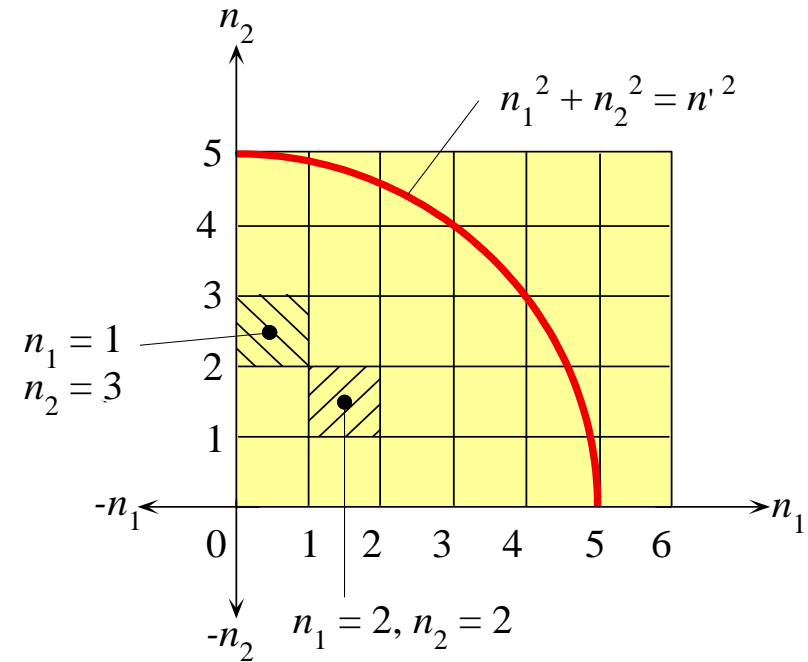
- k and +k are equivalent in k_x , k_y and k_z directions
- Number of k states within n' = Area of quarter circle with radius n' :

$$N'_{2D} = \frac{\pi n'^2}{4} = \frac{\pi 8ma^2}{4 h^2} E'$$

- Each state can carry a maximum of two electrons

- Maximum** Number of electrons /unit Area of material =
2 electrons * N'_{2D} /Area:

$$S_{2D}(E) = \frac{2 N'_{2D}}{a^2} = 2 \left[\frac{\pi 8m}{4 h^2} E' \right]$$



Each state, electron wavefunction in the crystal, can be represented by a box at n_1, n_2 .

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Density of States (3D)

- Number of k-states per unit area per unit volume within E' :

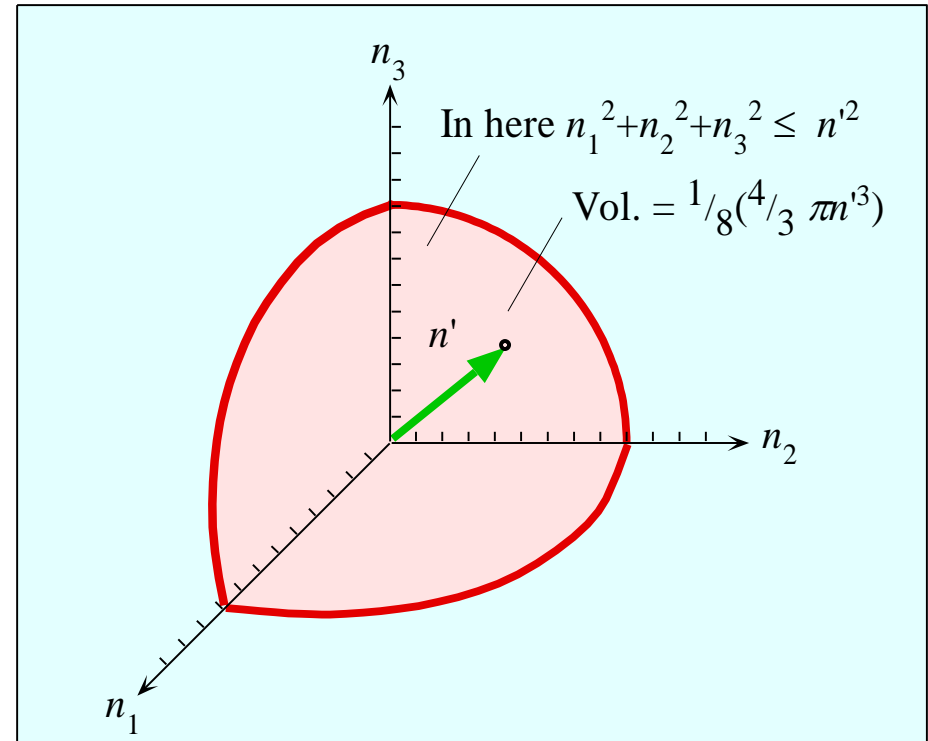
$$N'_{3D}(E') = \frac{\frac{4}{3}\pi n'^3}{8}$$

$$= \frac{\pi}{6} \left[\frac{8ma^2}{h^2} E' \right]^{3/2}$$

- Max.** Number of electrons within E' / unit Volume of material:

$$S_{3D}(E) = 2 \frac{N'_{3D}(E')}{a^3}$$

$$= \frac{\pi}{3} \left[\frac{8m}{h^2} E' \right]^{3/2}$$



In three dimensions, the volume defined by a sphere of radius n' and the positive axes n_1 , n_2 and n_3 , is all the possible combinations of positive n_1 , n_2 and n_3 , values which satisfy $n_1^2+n_2^2+n_3^2 \leq n'^2$.

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Density of States (3D)

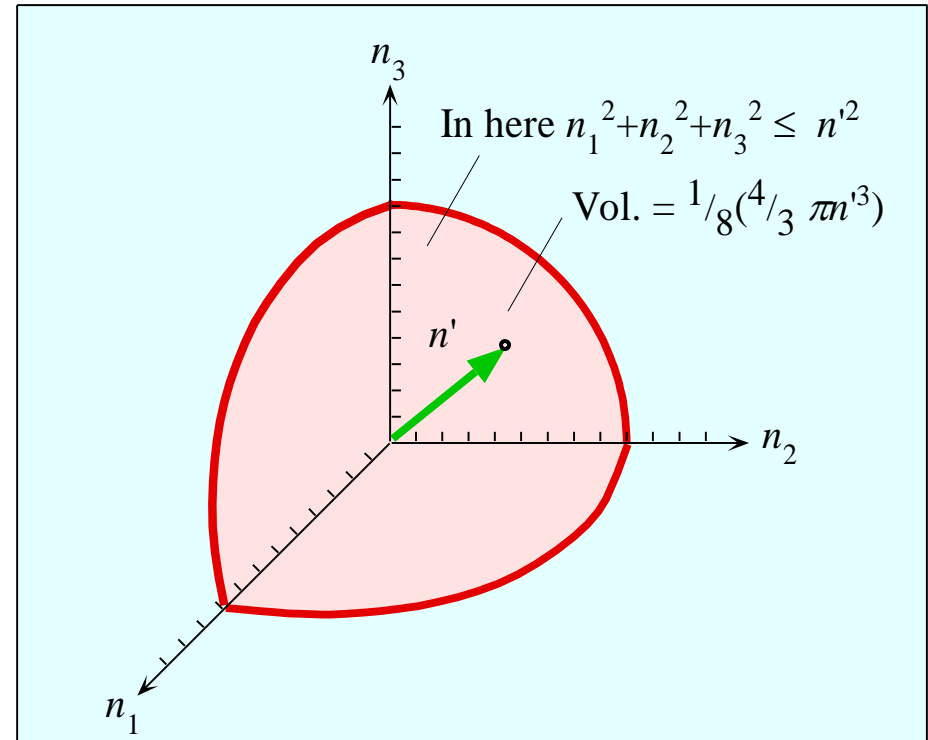
- Density of States = $g(E)$ = **Maximum** Number of electrons per unit **Energy** per unit **Volume**:

$$g_{3D}(E) = \frac{d}{dE} \left\{ \frac{N_{\text{electrons}}(E)}{\text{Vol}} \right\}$$

$$= \frac{d}{dE} \{S_{3D}(E)\}$$

$$= \frac{d}{dE} \left\{ \frac{\pi}{3} \left[\frac{8m}{h^2} E \right]^{\frac{3}{2}} \right\}$$

$$= (\pi/2) \left[\frac{8m}{h^2} \right]^{\frac{3}{2}} \{E^{1/2}\}$$



In three dimensions, the volume defined by a sphere of radius n' and the positive axes n_1 , n_2 and n_3 , is all the possible combinations of positive n_1 , n_2 and n_3 , values which satisfy $n_1^2 + n_2^2 + n_3^2 \leq n'^2$.

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Total Number of Electrons allowed between E1 and E2 on the E-K Diagram



$$N_{e,Total} = \int_{E1}^{E2} g(E) dE$$

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